

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
AKIHISA SHIMOMURA et al.) ATTN: New Applications
Based On: JP 2002-191493)
Filed: June 28, 2002)
For: METHOD OF MANUFACTURING)
A SEMICONDUCTOR DEVICE)

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing references known to Applicant and requests that these references be made of record in the above identified application. Copies of the references listed are submitted herewith in accordance with 37 C.F.R. 1.98(a).

U.S. Publication No. 2002/0048864 and U.S. Publication No. 2002/0004292 are in the family of JP 2001-144027.


U.S. Publication No. 2002/0014625 is in the family of JP 2002-124685.

U.S. Publication No. 2002/0006705 is in the family of JP 2002-083805.

U.S. Publication No. 2002/0098628 is in the family of JP 2002-324808.

The Commissioner is hereby authorized to charge fees under 37 C.F.R. §§1.16, 1.17, 1.20(a), 1.20(b), 1.20(c), and 1.20(d) (except the Issue Fee) which may be required now or hereafter, or credit any overpayment to Deposit Account No. 50-2280. A duplicate copy of this sheet is attached.

Respectfully submitted,


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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Based On	
				Filing Date	June 27, 2003
				First Named Inventor	Akihisa SHIMOMURA et al.
				Group Art Unit	
				Examiner Name	
Sheet	1	of	2	Attorney Docket Number	0756-7171

U.S. PATENT DOCUMENTS						
Examiner Initials ⁵	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
		6,165,876		Yamazaki et al.	12/26/2000	
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		2002/0098628	A1	Hamada et al.	07/25/2002	
		2002/0004292	A1	Yamazaki et al.	01/10/2002	

FOREIGN PATENT DOCUMENTS								
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		Office ³	Number ⁴	Kind Code ⁵ (if known)				
✓ ✓ ✓ ✓		JP	2001-144027			05/25/2001		Abst.
		JP	2002-124685			04/26/2002		Abst.
		JP	2002-083805			03/22/2002		Abst.
		JP	2002-324808			11/08/2002		U.S. equiv.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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	✓	Y. Mishima et al., "Implantation Temperature Effect on Polycrystalline Silicon by Ion Shower Doping," Journal of Applied Physics, Vol. 74, Dec. 15, 1993, No. 12, pp. 7114-7117	

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Sheet	2	of	2	Attorney Docket Number	
				0756-7171	

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	✓	Laviron et al., "Excimer-Laser Activation of Dopants in Silicon: A New Concept for a Uniform Treatment Over a Whole Die Area," International Workshop on Junction Technology, 2001, pp. 6-1-1 ~ 6-1-4	
	✓	Specification, drawings and pending claims of U.S. Application Serial No. 09/255,777 filed February 23, 1999, entitled SEMICONDUCTOR DEVICE AND METHOD FOR FORMING THE SAME	
	✓	Sasaki et al., "12.3: High Throughput CW-Laser Lateral Crystallization for Low-Temperature Poly-Si TFTs and Fabrication of 16 bit SRAMs and 270MHz Shift Registers," SID 02 DIGEST, pp. 154-157	

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